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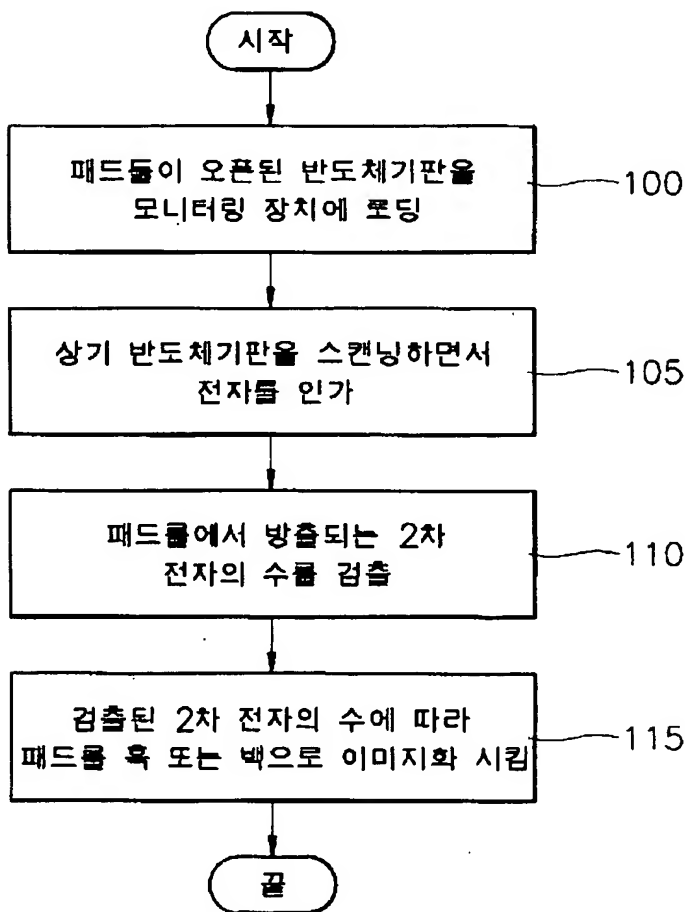
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(54) Title of Invention  
INLINE MONITORING METHOD OF SHALLOW PIT FORMED ON SEMICONDUCTOR SUBSTRATE

Representative drawing

(57) Abstract:



PURPOSE: An inline monitoring method of a shallow pit formed on a semiconductor substrate is provided to enhance reliability of a semiconductor device by performing correctly an inline monitoring method.

CONSTITUTION: A semiconductor substrate having opened pads is located on a sample location of a shallow pit monitoring device (100). A plurality of pads is opened on the semiconductor substrate. The loaded semiconductor substrate is scanned to an X-axis or a Y-axis and electron beams are emitted from an electron beam of a pit monitoring device to the plurality of pad(105). The loaded semiconductor substrate is irradiated by using the shallow pit monitoring device and the second electron detector detects the secondary electrons(110). A generating state of the shallow pit of the semiconductor substrate is checked by comparing the number of electrons of the neighboring pads to each other(115).

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